

# PSMN1R5-30YLC

# N-channel 30 V 1.55m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 17 May 2011

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	179	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static ch	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 12</u>		-	1.65	2.05	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12		-	1.3	1.55	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see Figure 14; see Figure 15	-	8.6	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $V_{DS}$ = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	30	-	nC

<sup>[1]</sup> Continuous current is limited by package.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

## 3. Ordering information

Table 3. Ordering information

Type number Package										
	Name	Description	Version							
PSMN1R5-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669							

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PSMN1R5-30YLC	1C530L

[1] % = placeholder for manufacturing site code

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{M}}$	<u>[1]</u>	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	[1]	-	100	Α
$I_{DM}$	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4		-	1008	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	179	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
$V_{ESD}$	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		1000	-	V
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1008	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 Ω; unclamped; see Figure 3		-	147	mJ

#### [1] Continuous current is limited by package.

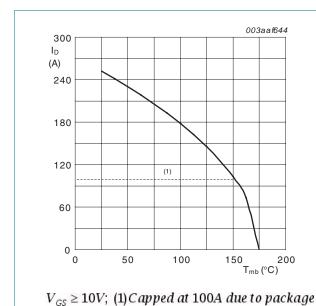


Fig 1. Continuous drain current as a function of mounting base temperature

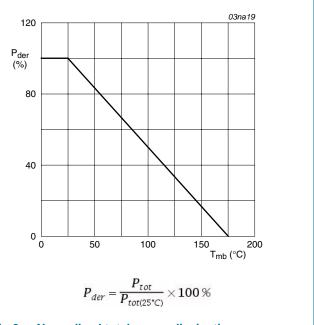


Fig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN1R5-30YLC

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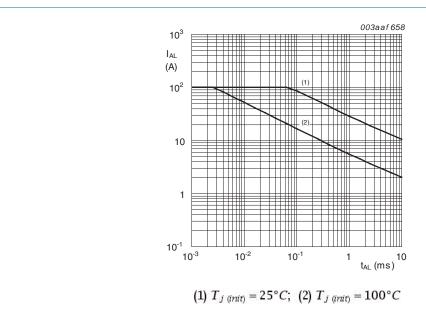
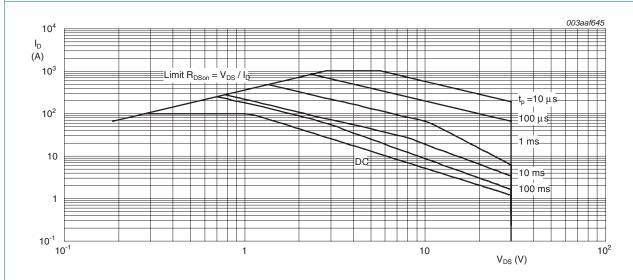


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



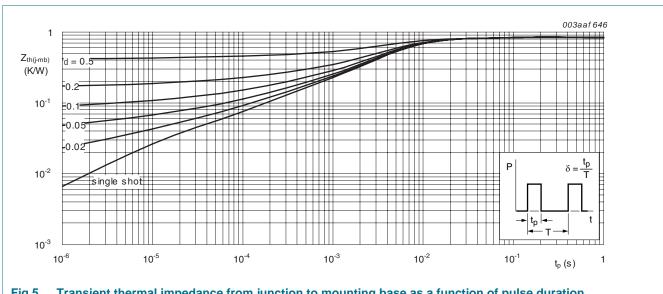
 $T_{mb} = 25$ °C;  $I_{DM}$  is a single pulse

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## **Thermal characteristics**

Table 6. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.71	0.84	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

## 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.51	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	1.65	2.05	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	3.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 12</u>	-	1.3	1.55	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	2.6	mΩ
$R_{G}$	gate resistance	f = 1 MHz	-	1.05	2.1	Ω
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	65	-	nC
		$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	30	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	53	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ;	-	9.7	-	nC
$Q_{GS(th)} \\$	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	6.6	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3.1	-	nC
$Q_{GD}$	gate-drain charge		-	8.6	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.53	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4044	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	860	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	287	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 0.6 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	33	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	62	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	62	-	ns
t <sub>f</sub>	fall time		-	38	-	ns

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	23	-	nC
Source-drain	diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	41	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	43	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 25 \text{ A};$	-	24	-	ns
t <sub>b</sub>	reverse recovery fall time	$dl_S/dt = -100 A/\mu s$ ; $V_{DS} = 15 V$ ; see Figure 18	-	17	-	ns

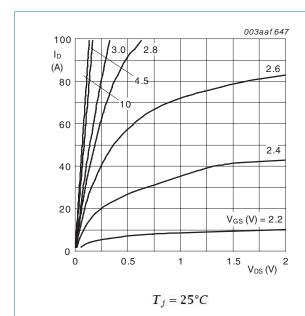
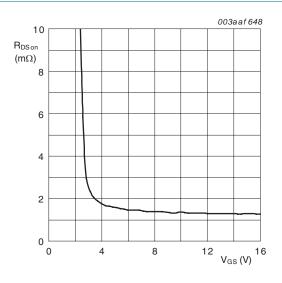


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 25A$ 

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

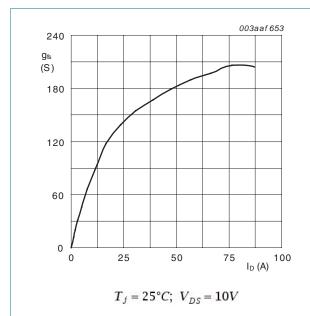


Fig 8. Forward transconductance as a function of drain current; typical values

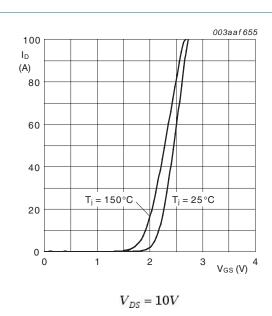


Fig 9. Transfer characteristics; drain-source current as a function of gate-source voltage; typical values

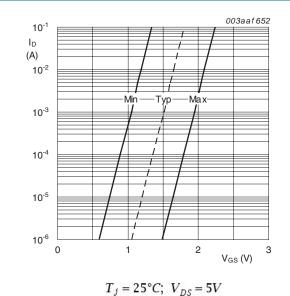


Fig 10. Sub-threshold drain current as a function of gate-source voltage

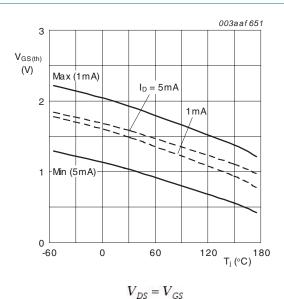


Fig 11. Gate-source threshold voltage as a function of junction temperature

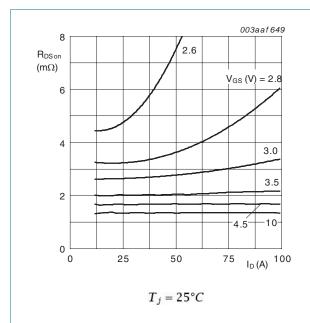


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

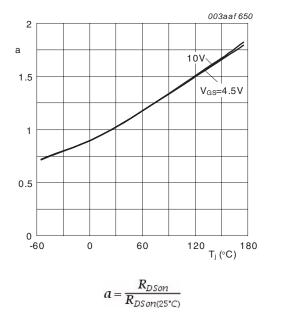


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

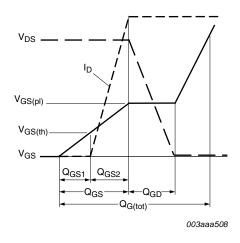
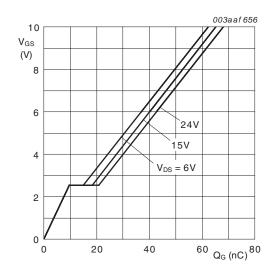
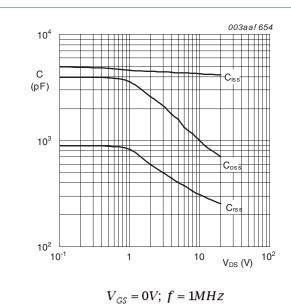


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values



values

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

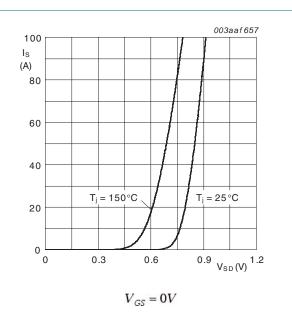


Fig 17. Source current as a function of source-drain voltage; typical values

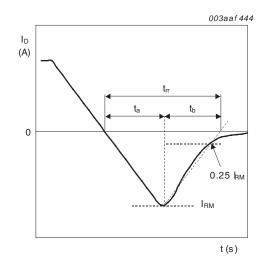
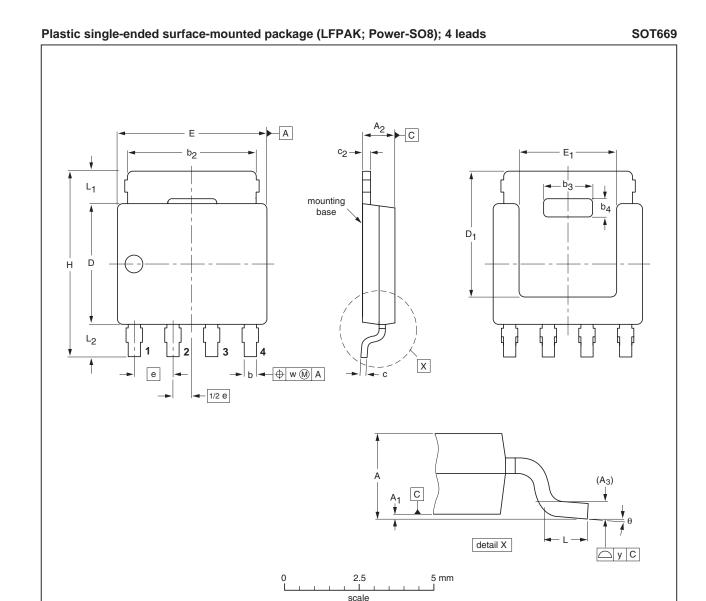


Fig 18. Reverse recovery timing definition

## 8. Package outline



#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b	b <sub>2</sub>	b <sub>3</sub>	b <sub>4</sub>	С	c <sub>2</sub>	D <sup>(1)</sup>	D <sub>1</sub> <sup>(1)</sup> max	E <sup>(1)</sup>	E <sub>1</sub> <sup>(1)</sup>	е	Н	L	L <sub>1</sub>	L <sub>2</sub>	w	у	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT669		MO-235				<del>06-03-16</del> 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN1R5-30YLC

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# 9. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R5-30YLC v.2	20110517	Product data sheet	-	PSMN1R9-25YLC v.1
Modifications:	<ul> <li>Various changes to</li> </ul>	content.		
PSMN1R9-25YLC v.1	20110502	Product data sheet	-	-

## 10. Legal information

#### 10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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# PSMN1R5-30YLC

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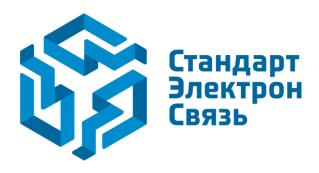
#### 11. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

## 12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking
5	Limiting values3
6	Thermal characteristics5
7	Characteristics6
8	Package outline
9	Revision history12
10	Legal information13
10.1	Data sheet status
10.2	Definitions13
10.3	Disclaimers
10.4	Trademarks14
11	Contact information 14



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С нами вы становитесь еще успешнее!

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